TOSHIBA Photocoupler Photorelay

# TLP197D

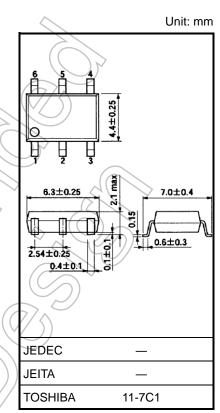
### PC Card Modems PBX Measurement Equipment

The Toshiba TLP197D consists of an infrared emitting diode optically coupled to a photo-MOSFET in a SOP package.

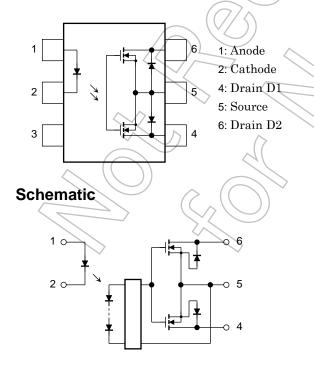
TLP197D is housed in a compact and thin SOP package and has characteristics of high-withstanding voltage and low ON-state resistance, which enable TLP197D to be applied in hook switches, dial-pulse switches for modems and facsimiles, and switches for test circuit switching in PBXs.

- 6-pin SOP (2.54SOP6): Height = 2.1 mm, pitch = 2.54 mm
- Normally open (1-form-A) device
- Peak OFF-state voltage: 200 V (min)
- Trigger LED current: 3 mA (max)
- ON-state current: 200 mA (max)
- ON-state resistance: 8  $\Omega$  (max)
- Isolation voltage: 1500 Vrms (min)
- UL-recognized: UL 1577, File No.E67349
- cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

## Pin Configuration (top view)



Weight: 0.13 g (typ.)



#### Absolute Maximum Ratings (Ta = 25°C)

|                             | Chara   | acteristics                | Symbol               | Rating | Unit   |                           |
|-----------------------------|---|----------------------------|----------------------|--------|--------|---------------------------|
|                             | Forward current                                 |                            | lF                   | 50     | mA     |                           |
|                             | Forward current derating (Ta≥25°C)              |                            | ∆IF/°C               | -0.5   | mA/°C  |                           |
|                             | Peak forward current<br>(100 μs pulse, 100 pps) |                            | IFP                  | 1      | А      | $\langle$                 |
| LED                         | Reverse voltage                                 |                            | VR                   | 5      | V      |                           |
|                             | Diode power diss                                | ipation                    | PD                   | 50     | mW     | (())                      |
|                             | Diode power diss                                | ipation derating (Ta≥25°C) | ∆P <sub>D</sub> /°C  | -0.5   | mW/°C  |                           |
|                             | Junction tempera                                | ture                       | Tj                   | 125    | °C     | $(\mathbb{Z}/\mathbb{Z})$ |
|                             | Off-state output to                             | erminal voltage            | Voff                 | 200    | V      |                           |
|                             |   | A connection               | ION                  | 200    | ((     |                           |
|                             | On-state current                                | B connection               |                      | 200    | mA     | $\mathcal{I}$             |
|                             |   | C connection               |                      | 400    |        |                           |
|                             | On-state current<br>derating<br>(Ta ≥25°C)      | A connection               | ∆l <sub>ON</sub> /°C | -2.0   |        |                           |
|                             |   | B connection               |                      | -2.0   | mA/°C  | 4                         |
| ctor                        |   | C connection               |                      | -4.0   | ())    | $\diamond (O)_{\alpha}$   |
| Detector                    | -   | A connection               |                      |        |        |                           |
|                             | Output power dissipation                        | B connection               | Po                   | 300    | > mW   | $\mathcal{C}$             |
|                             |   | C connection               | <                    |        |        |                           |
|                             | Output power                                    | A connection               |                      |        |        |                           |
|                             | dissipation<br>derating                         | B connection               | ∆Po/°C               | -3.0   | mW /ºC | $\langle / \rangle$       |
|                             | (Ta ≥ 25°C)                                     | C connection               | $\langle \rangle$    |        |        | $\sum$                    |
|                             | Junction tempera                                | ture                       | Ti                   | 125    | °C     |                           |
| Operating temperature range |   | Topr                       | -40 to 85            | °C     |        |                           |
| Storage temperature range   |   | Tstg                       | -55 to 125           | °C     |        |                           |
| Lead                        | Lead soldering temperature (10 s)               |                            | T <sub>sol</sub>     | 260    | °C     |                           |
|                             | tion voltage<br>60 s, R.H. ≤ 60 %               | ) (Note 1)                 | BVs                  | 1500   | Vrms   |                           |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

### **Recommended Operating Conditions**

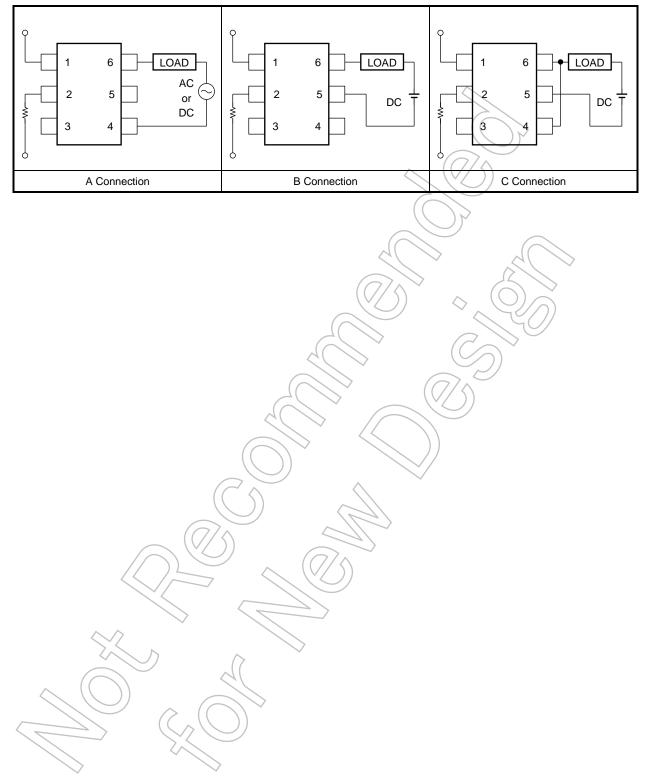
| Characteristics       | Symbol | Min | Тур. | Max | Unit |
|-----------------------|--------|-----|------|-----|------|
| Supply voltage        | VDD    | —   | _    | 160 | V    |
| Forward current       | lF     | 5   | 7.5  | 25  | mA   |
| On-state current      | ION    | —   | _    | 130 | mA   |
| Operating temperature | Topr   | -20 | _    | 60  | °C   |

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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### **Circuit Connections**



### **Electrical Characteristics (Ta = 25°C)**

|          | Characteristics   | Symbol         | Test Condition        | Min         | Тур. | Max | Unit |
|----------|-------------------|----------------|-----------------------|-------------|------|-----|------|
|          | Forward voltage   | VF             | $I_F = 10 \text{ mA}$ | 1.0         | 1.15 | 1.3 | V    |
| LED      | Reverse current   | I <sub>R</sub> | $V_R = 5 V$           |             | _    | 10  | μA   |
|          | Capacitance       | Ст             | VF = 0 V, f = 1 MHz   | $\setminus$ | 30   | _   | pF   |
| Detector | Off-state current | IOFF           | $V_{OFF} = 200 V$     |             |      | 1   | μA   |
| Dete     | Capacitance       | COFF           | V = 0 V, f = 1 MHz    |             | 100  |     | pF   |

# **Coupled Electrical Characteristics** (Ta = 25°C)

| Characteristics     |              | Symbol | Test Condition          | Min              | Тур. | Max | Unit |
|---------------------|--------------|--------|-------------------------|------------------|------|-----|------|
| Trigger LED current |              | IFT    | ION = 200 mA            |                  | 4    | ß   | mA   |
| Return LED current  |              | IFC    | loff = 100 μA           | 0.1              | Ń    |     | mA   |
|                     | A connection | Ron    | ION = 200 mA, IF = 5 mA | - <del>L</del> O | ))5  | 8   |      |
| On-state resistance | B connection |        | ION = 200 mA, IF = 5 mA | $\mathcal{A}$    | -3// | 5   | Ω    |
|                     | C connection |        | ION = 400 mA, IF = 5 mA |                  | 1.4  | _   |      |

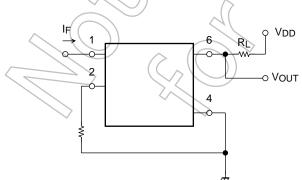
# **Isolation Characteristics (Ta = 25°C)**

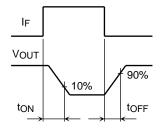
| Characteristics             | Symbol | Test Condition                      | Min                  | Тур.             | Max | Unit |
|-----------------------------|--------|-------------------------------------|----------------------|------------------|-----|------|
| Capacitance input to output | CS     | Vs = 0 V, f = 1 MHz                 | _                    | 0.8              | _   | pF   |
| Isolation resistance        | Rs     | V <sub>S</sub> = 500 V, R.H. ≤ 60 % | 5 × 10 <sup>10</sup> | 10 <sup>14</sup> | —   | Ω    |
| Isolation voltage           | BVs    | AC, 60 s                            | 1500                 | —                |     | Vrms |

# Switching Characteristics (Ta = $25^{\circ}$ C)

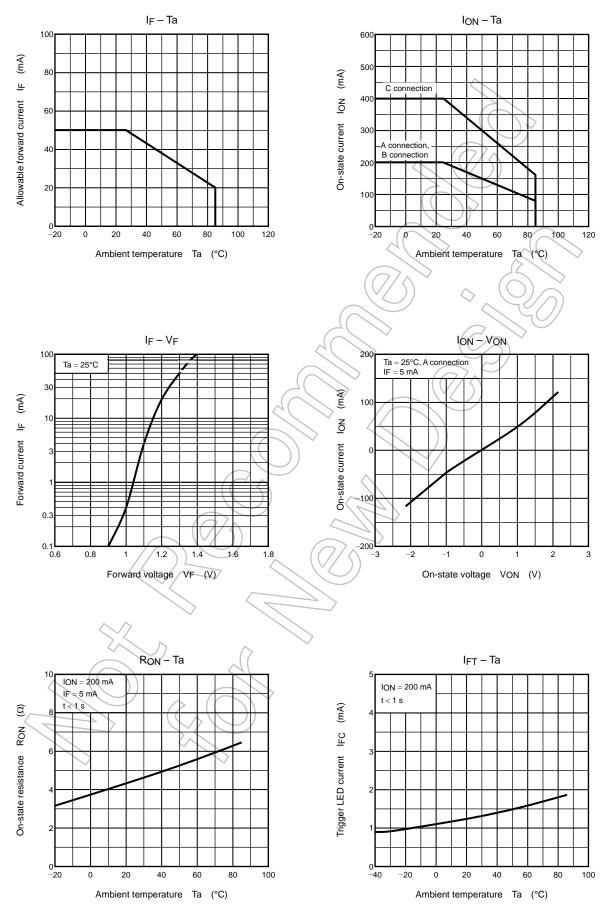
| Characteristics | Symbol Test Condition      |          | Min | Тур. | Max | Unit |
|-----------------|----------------------------|----------|-----|------|-----|------|
| Turn-on time    | ton $RL = 200 \Omega$      | (Note 2) | _   | 0.6  | 1.5 | ms   |
| Turn-off time   | toff VDD = 20 V, IF = 5 mA |          |     | 0.1  | 1.0 | ms   |

#### Note 2: Switching time test circuit



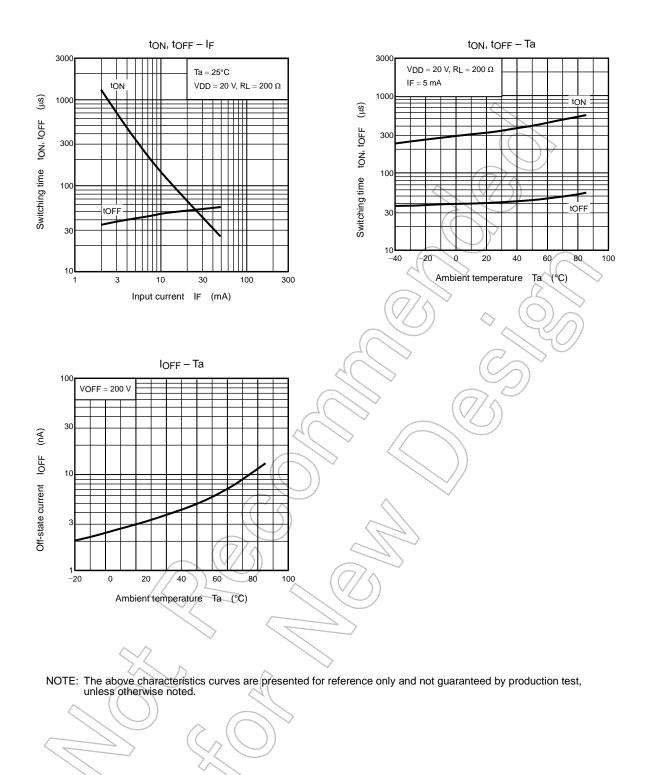


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NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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